

Silicon PNP Power Transistors

2SB1392

DESCRIPTION

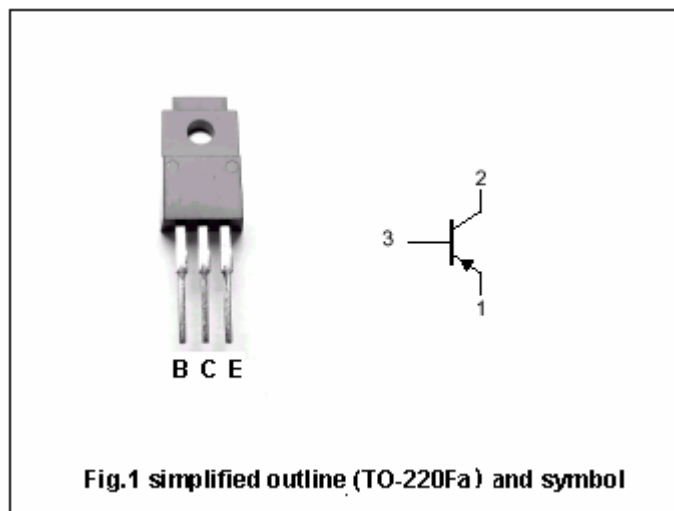
- With TO-220Fa package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-70	V
V_{CEO}	Collector -emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-4	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector power dissipation	$T_a=25^\circ\text{C}$	2.0	W
		$T_C=25^\circ\text{C}$	25	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; R_{BE}=\infty$	-60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-10\mu A; I_E=0$	-70			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-10\mu A; I_C=0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-1.2	V
V_{BE}	Base-emitter voltage	$I_C=-1A; V_{CE}=-4V$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-50V; I_E=0$			-10	μA
I_{CEO}	Collector cut-off current	$V_{CE}=-50V; R_{BE}=\infty$			-10	μA
h_{FE-1}	DC current gain	$I_C=-1A; V_{CE}=-4V$	60		200	
h_{FE-2}	DC current gain	$I_C=-0.1A; V_{CE}=-4V$	35			

◆ h_{FE-1} classifications

B	C
60-120	100-200

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PACKAGE OUTLINE

